

Title (en)

EEPROM MEMORY CELL FOR HIGH TEMPERATURES

Title (de)

EEPROM-SPEICHERZELLE FÜR HOHE TEMPERATUREN

Title (fr)

CELLULE DE MEMOIRE EEPROM DESTINEE A DES TEMPERATURES ELEVEES

Publication

**EP 1723669 A1 20061122 (DE)**

Application

**EP 05716998 A 20050310**

Priority

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Abstract (en)

[origin: WO2005088705A1] The invention relates to an EEPROM memory cell for using at high temperatures, said memory cell being produced by SOI technology. An EEPROM cell for high temperatures consists of three MOS transistors. The inventive EEPROM cell is formed from a memory transistor comprising a floating gate and a high-voltage transistor provided with a body connection that can be freely occupied. A constructive change in the structure of the high-voltage transistor enables the use of a third transistor in the memory cell to be avoided, reducing the surface of the semiconductor wafer and thus also costs.

IPC 8 full level

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CPC (source: EP US)

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